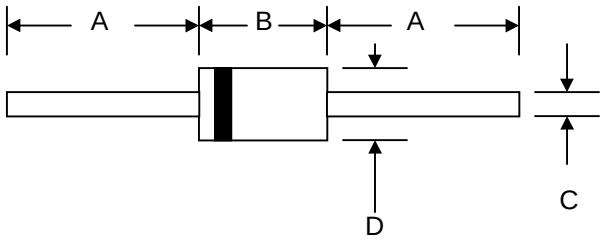
DB3

SILICON BIDIRECTIONAL DIACS

Features

- VBO:28-36V
- Low Breakover Current



Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free: For RoHS / Lead Free Version,**

DO-41		
Dim	**Min**	**Max**
A	25.4	—
B	4.06	5.21
C	0.70	0.90
D	2.00	2.72
All Dimensions in mm		

DO-35		
Dim	**Min**	**Max**
A	27.5	—
B	—	3.8
C	0.50	0.60
D	—	2.0
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C

ABSOLUTE RATINGS			
PARAMETERS	SYMBOL	VALUE	UNITS
		DB3	
Power Dissipation on Printed Cir cuit(L=10mm) T_A=50℃	Pc	150	mW
Repetitive Peak on-state Current Tp=10uS f=100Hz	I_{TRM}	2.0	A
Storage and Operating Juntion Temperature	T_{STG}/T_J	-40 to +125	℃

ELECTRICAL CHARACTERISTICS					
PAPRAMETERS	SYMBOLS	TEST CONDITIONS		VALUE	UNITS
				DB3	
Breakover Voltage*	V_{BO}	C=22nf** See Diagram 1	Min	28	V
			Typ	32	
			Max	36	
Breakover Voltage Symmetry	1+V_{BO}I- 1-V_{BO}I	C=22nf** See Diagram 1	Max	±3	V
Dynamic Breakover Voltage	1±△V1	△I=(I_{BO} to IF=10mA) See FIG 1	Min	5	V
Output Voltage*	V_O	See FIG 2	Min	5	V
Breakover Current*	I_{BO}	C=22nf**	Max	100	uA
Rise Time*	tr	See FIG 3	Typ	1.5	uS
Leakage Current*	I_B	I_B=0.5 V_{BO} MAX See FIG 3	Max	10	uA

NOTE:* Electrical characteristics applicable in both forward and reverse directions.

** Connected in parallel with the devices.

FIG.1-CURRENT-VOLTAGE CHARACTERISTICS

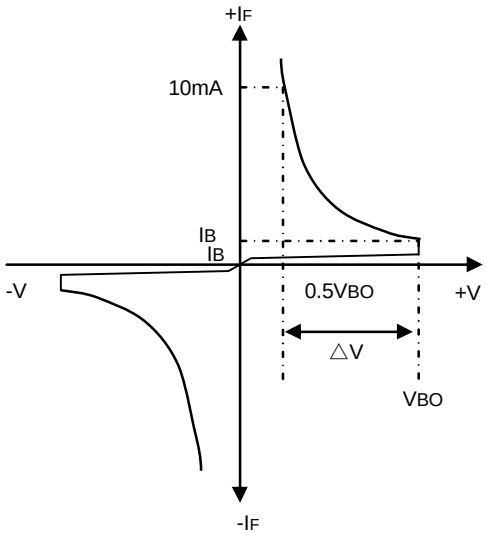


FIG.2-TEST CIRCUIT FOR OUTPUT VOLATGE

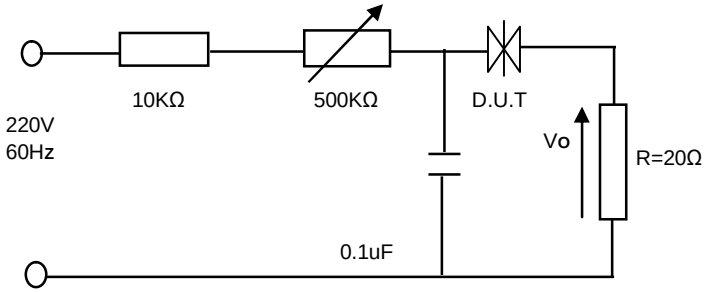


FIG.3-TEST CIRCUIT SEE FIG.2 ADJUST R
FOR Ip=0.5A

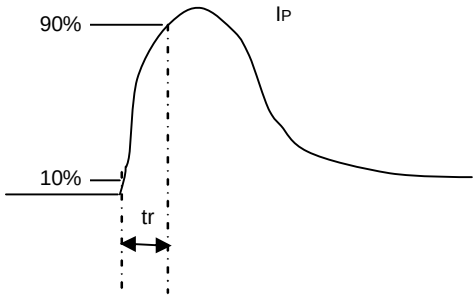


FIG.4-TEST CIRCUIT FOR OUTPUT

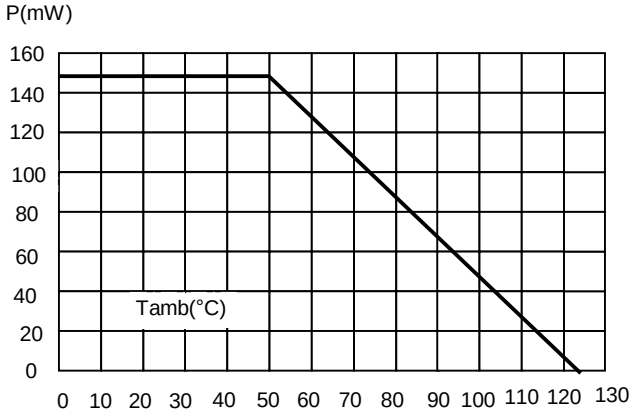


FIG.5-RELATIVE VARIATION OF VBO VERSUS
JUNCTION TEMPERATURE(TYPICAL VALUES)

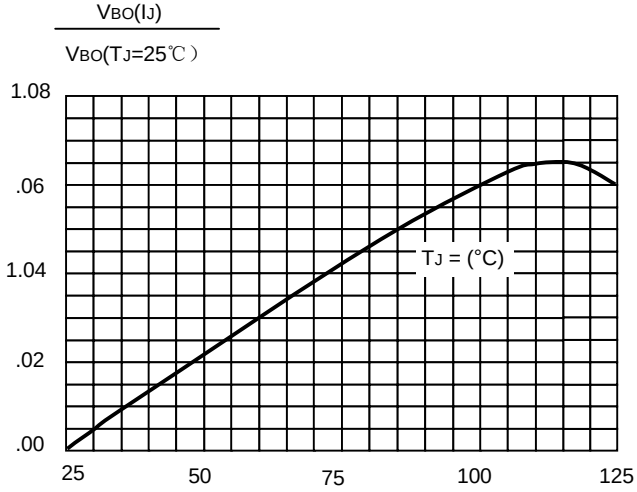


FIG.6-PEAK PULSE CURRENT VERSUS PULSE
DURATION (MAXIMUM VALUES)